

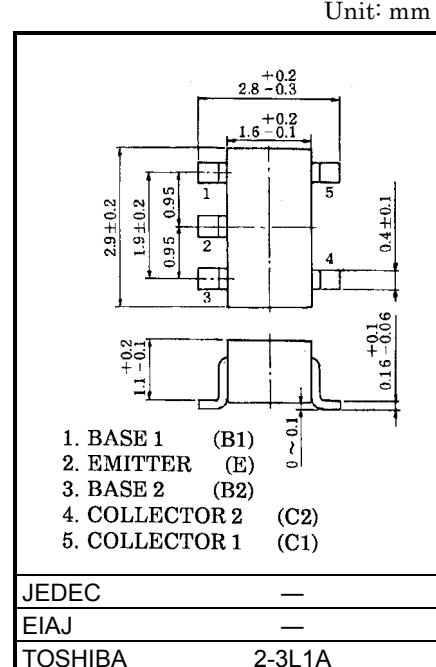
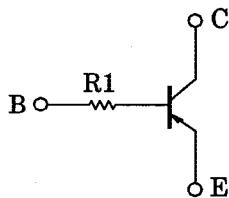
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2510,RN2511

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

- Including twodevices in SMV (super mini type with 5 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1510, RN1511

Equivalent Circuit

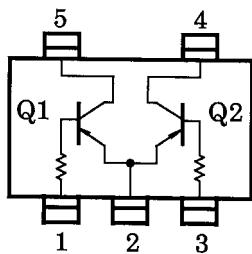


Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector power dissipation	P_C^*	300	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$

* : Total rating

Equivalent Circuit (Top View)



Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit	
Collector cut-off current	I_{CBO}	—	$V_{CB} = -50\text{V}$, $I_E = 0$	—	—	-100	nA	
Emitter cut-off current	I_{EBO}	—	$V_{EB} = -5\text{V}$, $I_C = 0$	—	—	-100	nA	
DC current gain	h_{FE}	—	$V_{CE} = -5\text{V}$, $I_C = -1\text{mA}$	120	—	400	—	
Collector-emitter saturation voltage	$V_{CE}(\text{sat})$	—	$I_C = -5\text{mA}$, $I_B = -0.25\text{mA}$	—	-0.1	-0.3	V	
Translation frequency	f_T	—	$V_{CE} = -10\text{V}$, $I_C = -5\text{mA}$	—	250	—	MHz	
Collector output capacitance	C_{ob}	—	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$	—	3	6	pF	
Input resistor	RN2510	R1	—	—	3.29	4.7	6.11	kΩ
	RN2511				7	10	13	

(Q1, Q2 Common)

